Surface Mount Transient Voltage Suppressor Diode

Features

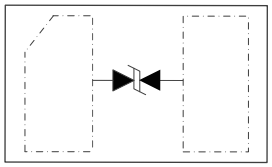
- ✧ Bi-directional ESD protection of one line
- ✧ Solid-state silicon-avalanche technology
- ✧ Working Voltage: 4.4V
- ✧ Peak Power up to 400 Watts @ 8 x 20μs Pulse
- ✧ Low Leakage current
- ✧ IEC 61000-4-2 (ESD) ±30kV (air), ±30kV (contact)
- ✧ IEC 61000-4-4 (EFT) 40A (5/50ns)

Applications

- ✧ Cellular Handsets & Accessories
- ✧ Portable devices
- ✧ Digital cameras
- ✧ Power supplies

Mechanical Data

- ✧ UL Flame Rating : UL94V-0
- ✧ Reel Size : 7 inch
- ✧ RoHS/WEEE Compliant



Circuit Diagram



DFN1006

Absolute Maximum Rating at T_A = 25 °C, unless otherwise specified

Rating	Symbol	Value	Units
Peak Pulse Power (t_p =8/20μs)	P_{PP}	400	Watts
Peak Pulse Current (t_p =8/20μs)	I_{pp}	40	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	±30 ±30	kV
Lead Soldering Temperature	T_L	260(10seconds)	℃
Junction Temperature	T_J	-55 to + 125	℃
Storage Temperature	T_{stg}	-55 to + 150	℃

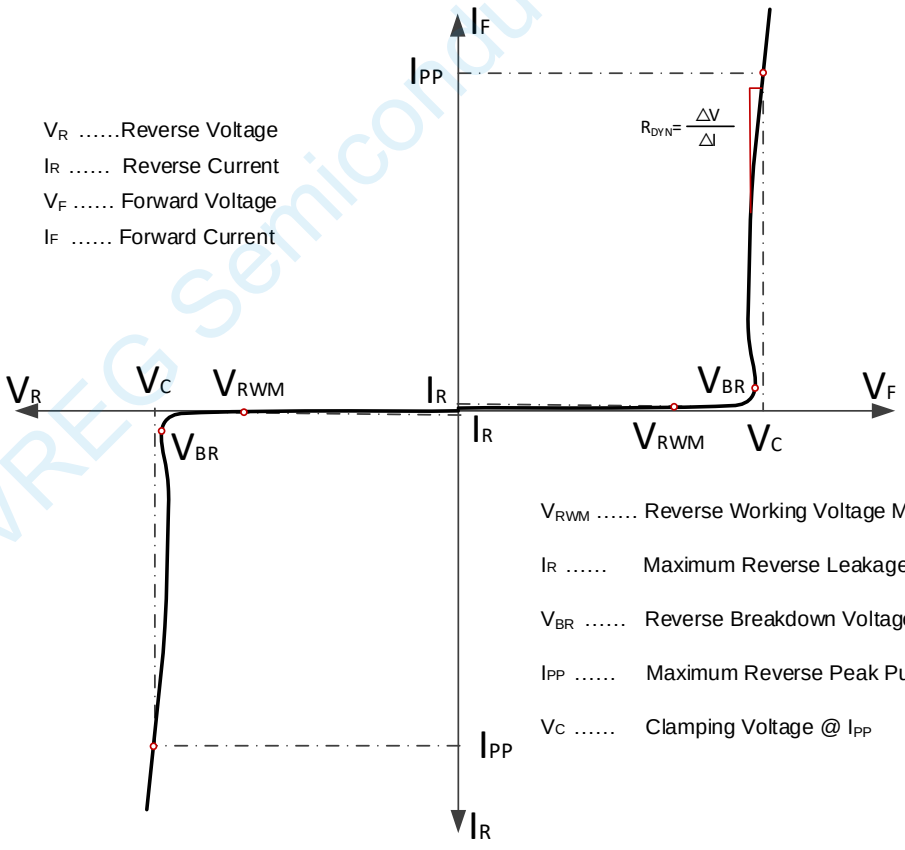
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Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typical	Max.	Units
Reverse Stand-Off Voltage	V_{RWM}				4.4	V
Reverse Breakdown Voltage	V_{BR}	I_T=1mA	4.5		6.5	V
Reverse Leakage Current	I_R	V_{RWM}=4.4V, T=25℃			500	nA
Peak Pulse Current	I_{PP}	tp =8/20μs			40	A
Clamping Voltage	V_C	I_{PP}=10A, tp=8/20μs		5.3	5.5	V
Clamping Voltage	V_C	I_{PP}=40A, tp=8/20μs		9.7	10	V
Junction Capacitance	C_J	V_R = 0V, f = 1MHz		95	100	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
1. All parameters specified at T_A = 25°C unless otherwise noted.
2. These parameters are guaranteed by design and characterization.
3. Standard IEC 61000−4−2 with $C_{Discharge}$ = 150 pF, $R_{Discharge}$ = 330 Ω

Electrical Parameters at T_A = 25 °C, unless otherwise specified



V_{RWM} ..... Reverse Working Voltage Max.

I_R ..... Maximum Reverse Leakage Current @ V_{RWM}

V_{BR} ..... Reverse Breakdown Voltage

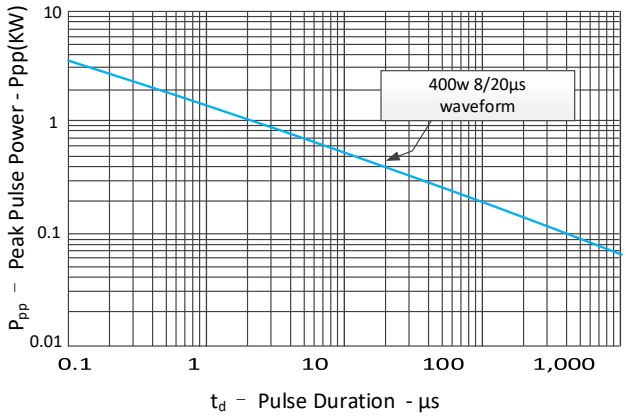
I_{PP} ..... Maximum Reverse Peak Pulse Current

V_C ..... Clamping Voltage @ I_{PP}

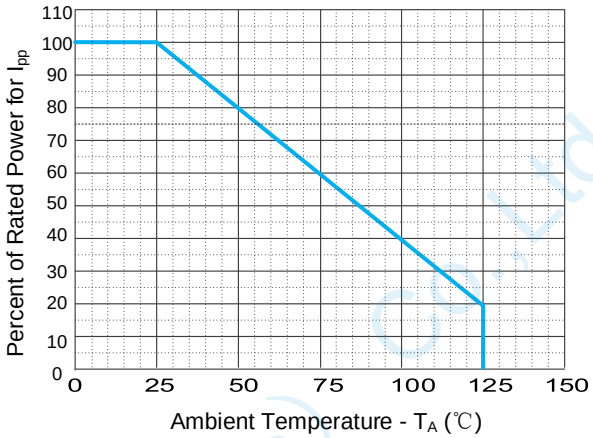
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Typical Characteristics at T_A = 25 °C, unless otherwise specified

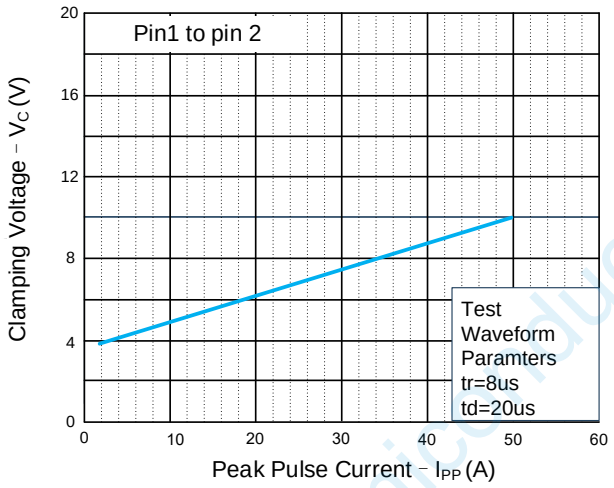
Peak Pulse Power vs. Pulse Time



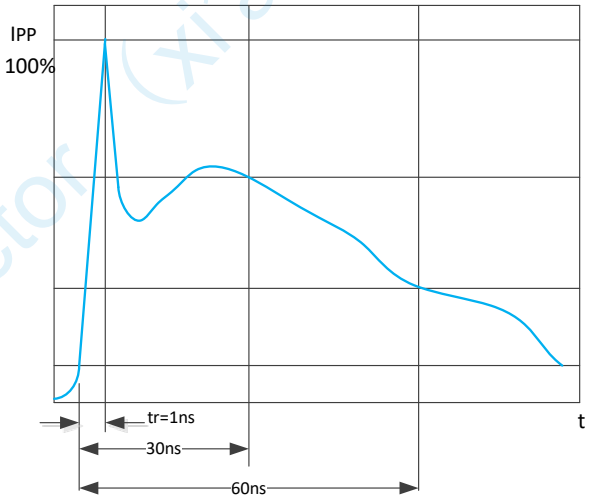
Power derating vs. Ambient temperature



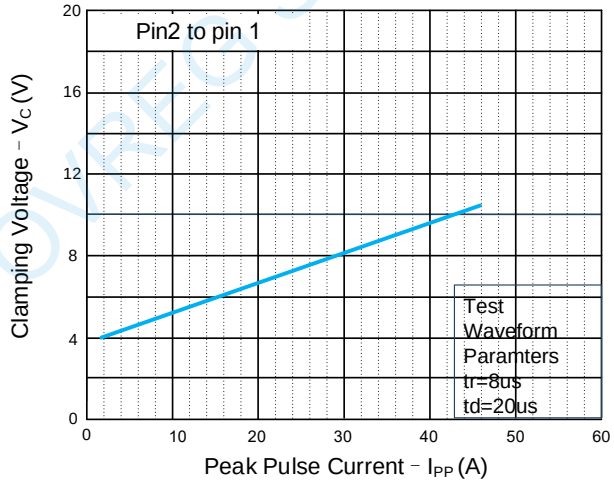
Forward Clamping Voltage vs. peak PulseCurrent



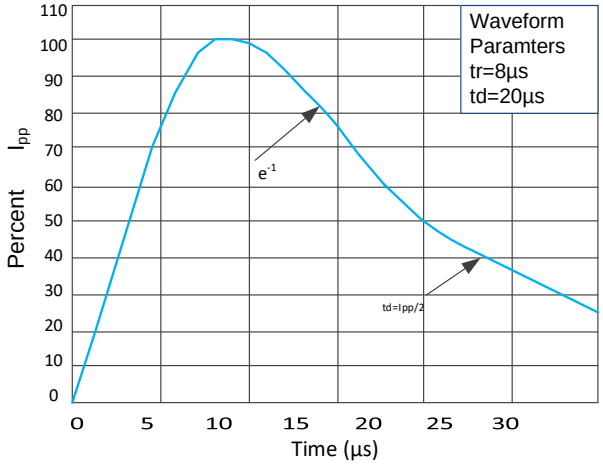
IEC61000-4-2 +8kV Pulse Waveform



Reverse Clamping Voltage vs. peak PulseCurrent



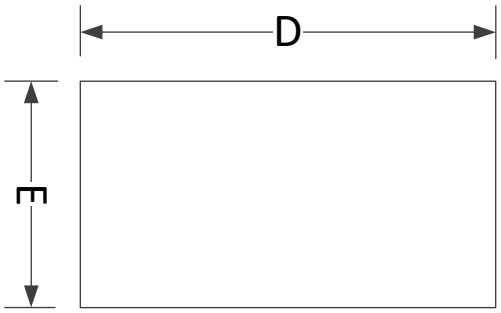
8/20uS Pulse Waveform



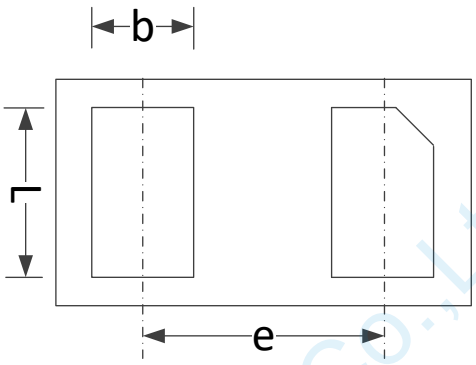
10%

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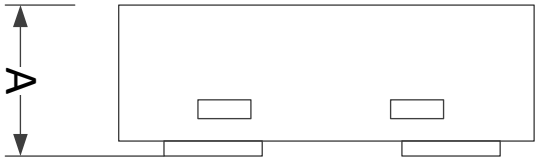
Package Information



TOP VIEW



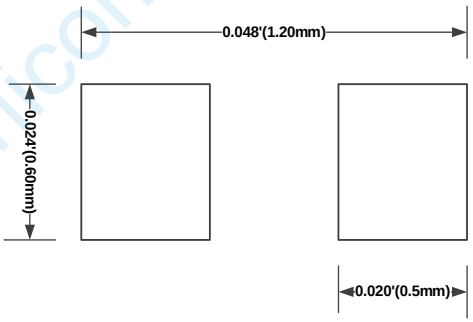
BOTTOM VIEW



SIDE VIEW

COMMON DIMENSION (MM)			
PKG	DFN1006		
REF.	MIN.	NOM.	MAX.
A	0.43	-	0.53
b	0.20	0.25	0.30
L	0.45	0.50	0.55
e	0.65REF		
D	0.95	1.00	1.05
E	0.55	0.60	0.65

Recommend PCB Layout



Notes: This PCB Layout Is For Reference Purposes Only

Marking

VF

Ordering Information

Part number	Material	Type	Reel size	MOQ	MOQ/internal box	MOQ/carton
OVE11E32F1M	GREEN	T/R	7 inch	12k/reel	10reel= 120k/box	4boxes=480k/carton

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